

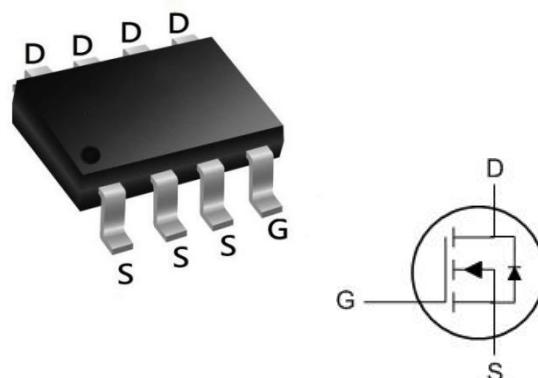

**Product Summary**

BVDSS	RDS(ON)	ID
40V	12 mΩ	9A

**SOP8 Pin Configuration**
**Description**

The XXW4009 is the high cell density trenched N-ch MOSFETs, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications.

The XXW4009 meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.


**Absolute Maximum Ratings ( $T_C=25^\circ\text{C}$  unless otherwise noted)**

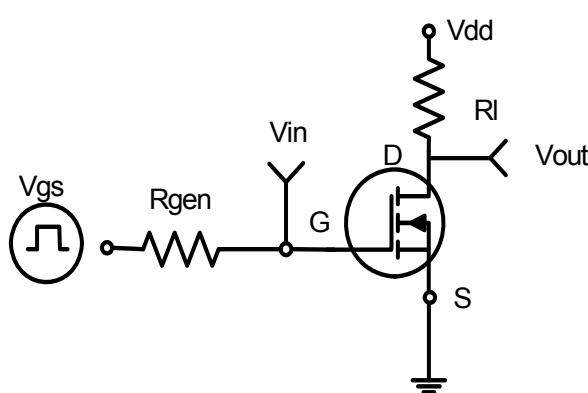
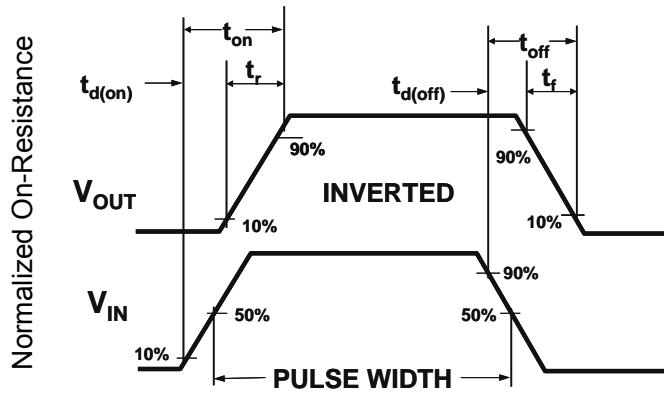
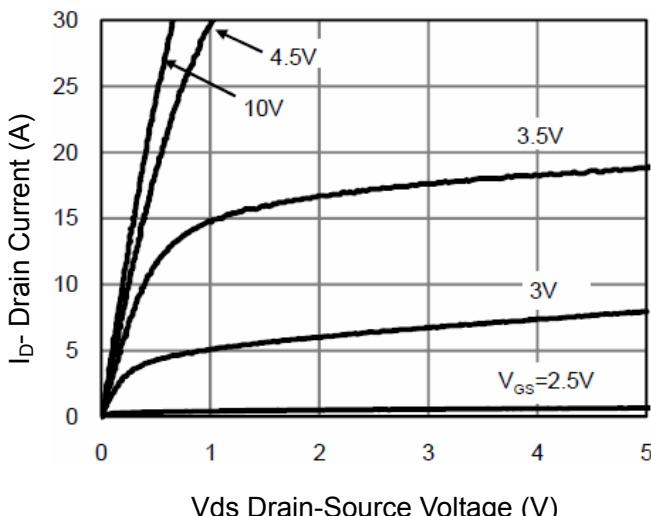
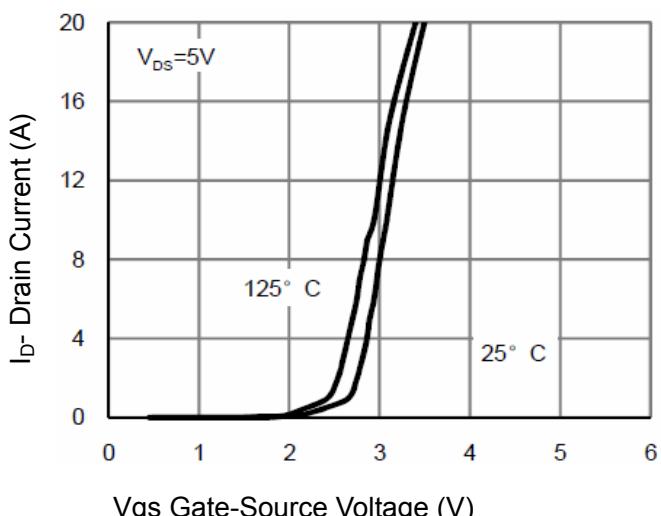
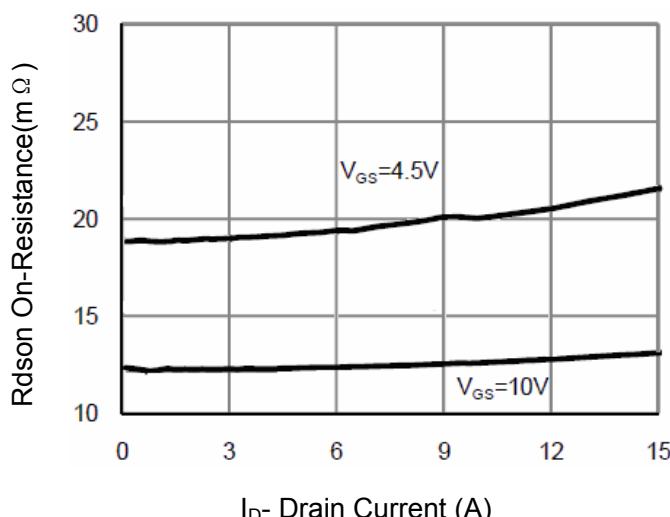
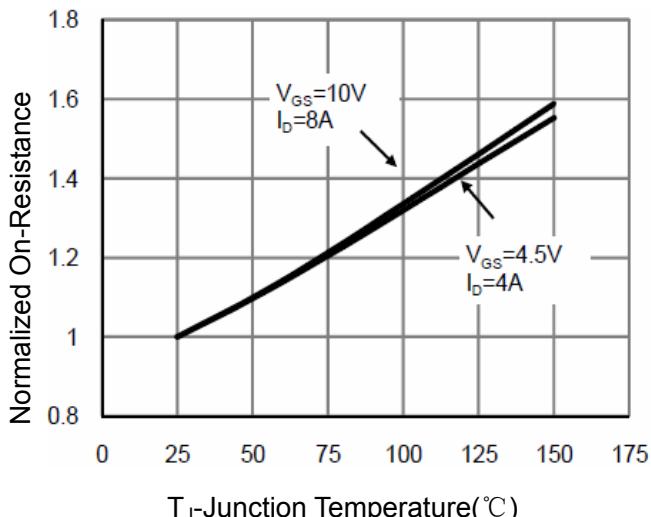
Parameter	Symbol	Limit	Unit
Drain-Source Voltage	$V_{DS}$	40	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Drain Current-Continuous	$I_D$	9	A
Drain Current-Continuous( $T_C=100^\circ\text{C}$ )	$I_D(100^\circ\text{C})$	6.4	A
Pulsed Drain Current	$I_{DM}$	40	A
Maximum Power Dissipation	$P_D$	2	W
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 To 150	°C

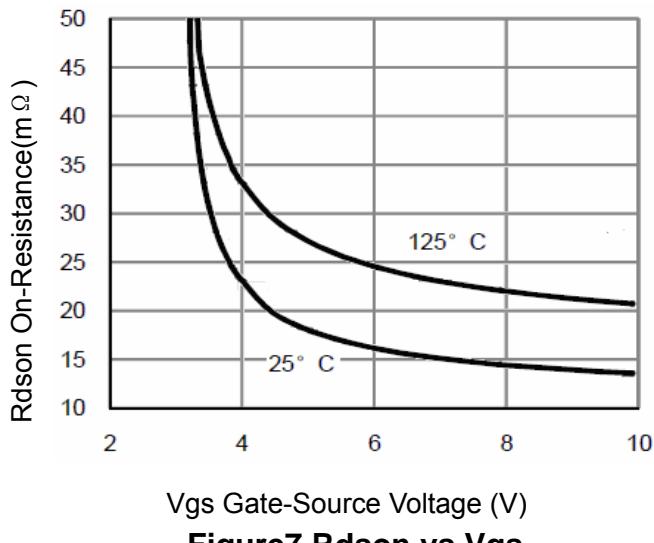
**Thermal Characteristic**

Thermal Resistance, Junction-to-Ambient <sup>(Note 2)</sup>	$R_{\theta JA}$	62.5	°C/W
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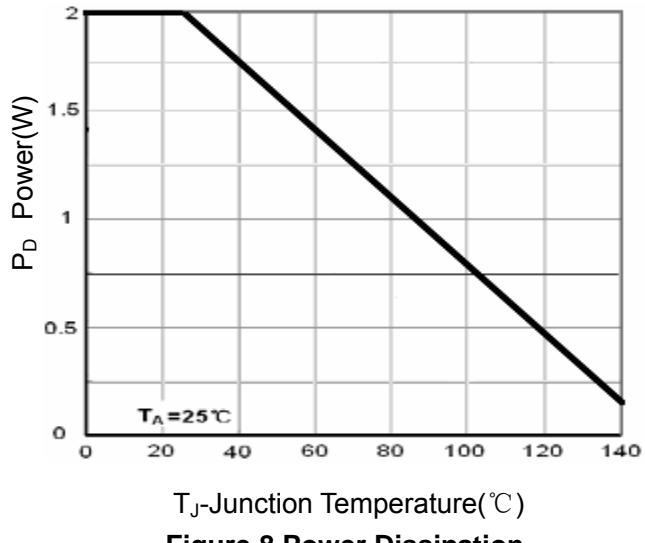
**N-Ch 40V Fast Switching MOSFETs**
**N-CH Electrical Characteristics ( $T_A=25^\circ\text{C}$  unless otherwise noted)**

Parameter	Symbol	Condition	Min	Typ	Max	Unit
<b>Off Characteristics</b>						
Drain-Source Breakdown Voltage	$\text{BV}_{\text{DSS}}$	$V_{\text{GS}}=0\text{V}, I_{\text{D}}=250\mu\text{A}$	40	-	-	V
Zero Gate Voltage Drain Current	$I_{\text{DSS}}$	$V_{\text{DS}}=40\text{V}, V_{\text{GS}}=0\text{V}$	-	-	1	$\mu\text{A}$
Gate-Body Leakage Current	$I_{\text{GSS}}$	$V_{\text{GS}}=\pm20\text{V}, V_{\text{DS}}=0\text{V}$	-	-	$\pm100$	nA
<b>On Characteristics</b> <sup>(Note 3)</sup>						
Gate Threshold Voltage	$V_{\text{GS}(\text{th})}$	$V_{\text{DS}}=V_{\text{GS}}, I_{\text{D}}=250\mu\text{A}$	1	1.5	2.0	V
Drain-Source On-State Resistance	$R_{\text{DS}(\text{ON})}$	$V_{\text{GS}}=10\text{V}, I_{\text{D}}=8\text{A}$	-	12	16	$\text{m}\Omega$
		$V_{\text{GS}}=4.5\text{V}, I_{\text{D}}=4\text{A}$	-	19	24	$\text{m}\Omega$
Forward Transconductance	$g_{\text{FS}}$	$V_{\text{DS}}=5\text{V}, I_{\text{D}}=8\text{A}$	33	-	-	S
<b>Dynamic Characteristics</b> <sup>(Note 4)</sup>						
Input Capacitance	$C_{\text{iss}}$	$V_{\text{DS}}=20\text{V}, V_{\text{GS}}=0\text{V}, F=1.0\text{MHz}$	-	964	-	PF
Output Capacitance	$C_{\text{oss}}$		-	109	-	PF
Reverse Transfer Capacitance	$C_{\text{rss}}$		-	96	-	PF
<b>Switching Characteristics</b> <sup>(Note 4)</sup>						
Turn-on Delay Time	$t_{\text{d}(\text{on})}$	$V_{\text{DD}}=20\text{V}, R_{\text{L}}=2.5\Omega, V_{\text{GS}}=10\text{V}, R_{\text{GEN}}=3\Omega$	-	5.5	-	nS
Turn-on Rise Time	$t_{\text{r}}$		-	14	-	nS
Turn-Off Delay Time	$t_{\text{d}(\text{off})}$		-	24	-	nS
Turn-Off Fall Time	$t_{\text{f}}$		-	12	-	nS
Total Gate Charge	$Q_{\text{g}}$	$V_{\text{DS}}=20\text{V}, I_{\text{D}}=8\text{A}, V_{\text{GS}}=10\text{V}$	-	22.9	-	nC
Gate-Source Charge	$Q_{\text{gs}}$		-	3.5	-	nC
Gate-Drain Charge	$Q_{\text{gd}}$		-	5.3	-	nC
<b>Drain-Source Diode Characteristics</b>						
Diode Forward Voltage <sup>(Note 3)</sup>	$V_{\text{SD}}$	$V_{\text{GS}}=0\text{V}, I_{\text{S}}=9\text{A}$	-	0.8	1.2	V

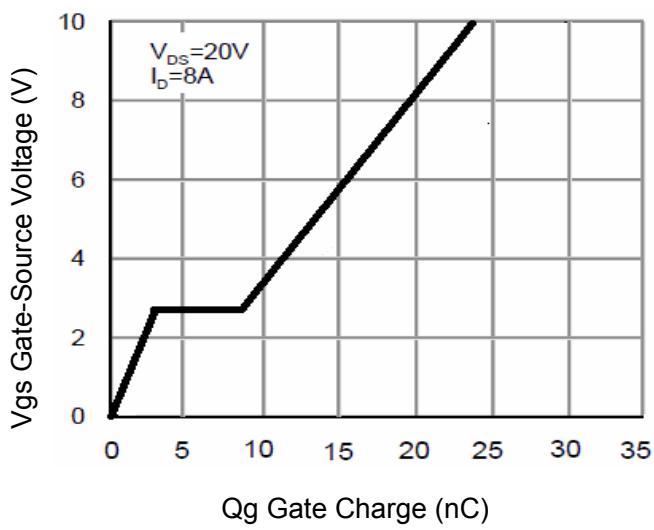
**N-Channel Typical Electrical and Thermal Characteristics (Curves)**

**Figure 1:Switching Test Circuit**

**Figure 2:Switching Waveforms**

**Figure 3 Output Characteristics**

**Figure 4 Transfer Characteristics**

**Figure 5 Drain-Source On-Resistance**

**Figure 6 Drain-Source On-Resistance**



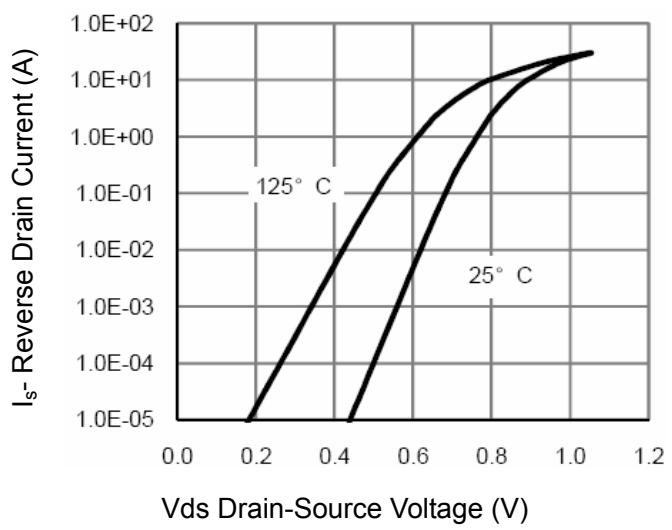
**Figure 7 Rdson vs Vgs**



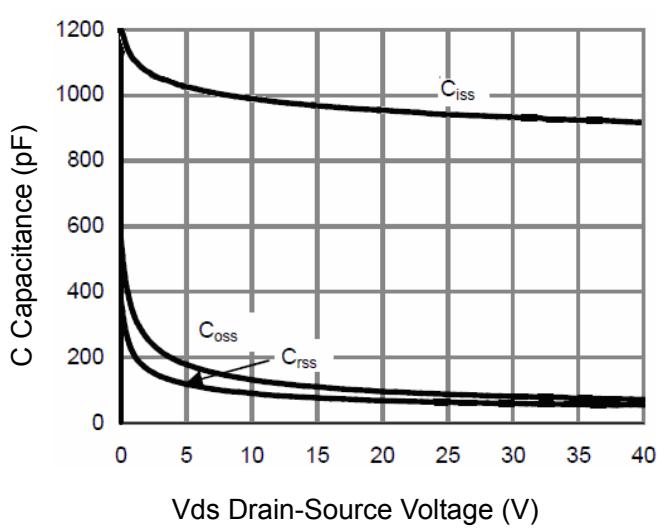
**Figure 8 Power Dissipation**



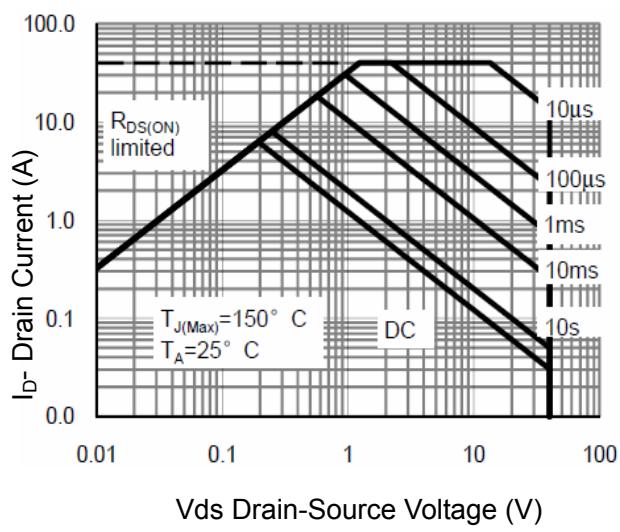
**Figure 9 Gate Charge**



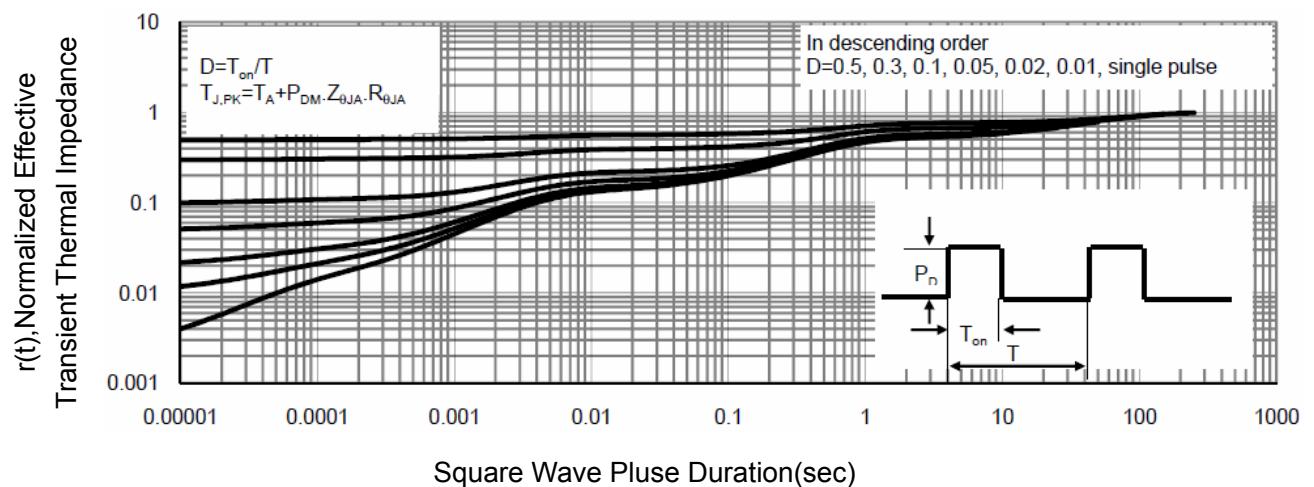
**Figure 10 Source- Drain Diode Forward**



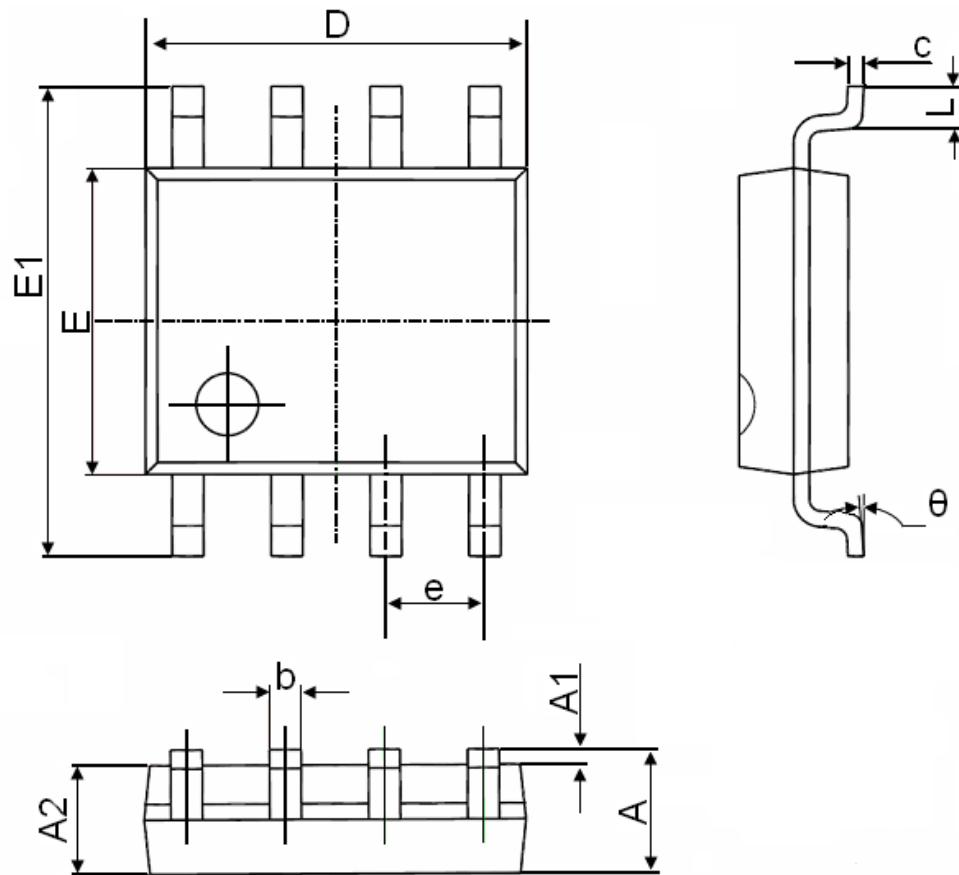
**Figure 11 Capacitance vs Vds**



**Figure 12 Safe Operation Area**



**Figure 13 Normalized Maximum Transient Thermal Impedance**

**SOP-8 Package Information**


Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.006	0.010
D	4.700	5.100	0.185	0.200
E	3.800	4.000	0.150	0.157
E1	5.800	6.200	0.228	0.244
e	1.270(BSC)		0.050(BSC)	
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°